



**N-channel Enhancement-mode Power MOSFET**

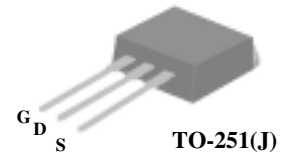
- Simple Drive Requirement**
- Supports 2.5V Gate Drive**
- Lower Gate Charge**
- RoHS-compliant**



$BV_{DSS}$	20V
$R_{DS(ON)}$	50mΩ
$I_D$	12.5A

**Description**

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, low on-resistance and cost-effectiveness.



**Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	20	V
$V_{GS}$	Gate-Source Voltage	±16	V
$I_D$ at $T_A=25\text{ }^\circ\text{C}$	Continuous Drain Current <sup>3</sup>	12.5	A
$I_D$ at $T_A=100\text{ }^\circ\text{C}$	Continuous Drain Current <sup>3</sup>	8	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	60	A
$P_D$ at $T_A=25\text{ }^\circ\text{C}$	Total Power Dissipation	12.5	W
	Linear Derating Factor	0.1	W/°C
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C

**Thermal Data**

Symbol	Parameter	Value	Unit
Rthj-a	Maximum Thermal Resistance, Junction-case	10	°C/W
Rthj-c	Maximum Thermal Resistance, Junction-ambient	110	°C/W

**Ordering Information**

- AP9T15GH-3TR**      **RoHS-compliant TO-252 shipped on tape and reel (3000 pcs/reel)**
- AP9T15GJ-3TB**      **RoHS-compliant TO-251 shipped in tubes**



**Electrical Specifications at  $T_j=25^\circ\text{C}$  (unless otherwise specified)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	20	-	-	V
$\Delta BV_{DSS} / \Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to $25^\circ\text{C}, I_D=1\text{mA}$	-	0.02	-	V/ $^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=4.5V, I_D=6A$	-	-	50	m $\Omega$
		$V_{GS}=2.5V, I_D=5.2A$	-	-	80	m $\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5	-	1.5	V
$g_{fs}$	Forward Transconductance	$V_{DS}=5V, I_D=10A$	-	10	-	S
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=20V, V_{GS}=0V$	-	-	1	$\mu A$
	Drain-Source Leakage Current ( $T_j=150^\circ\text{C}$ )	$V_{DS}=16V, V_{GS}=0V$	-	-	25	$\mu A$
$I_{GSS}$	Gate-Source Leakage	$V_{GS}=\pm 16V$	-	-	$\pm 100$	nA
$Q_g$	Total Gate Charge <sup>2</sup>	$I_D=10A$	-	5	8	nC
$Q_{gs}$	Gate-Source Charge	$V_{DS}=16V$	-	1	-	nC
$Q_{gd}$	Gate-Drain ("Miller") Charge	$V_{GS}=4.5V$	-	2	-	nC
$t_{d(on)}$	Turn-on Delay Time <sup>2</sup>	$V_{DS}=10V$	-	8	-	ns
$t_r$	Rise Time	$I_D=10A$	-	55	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega, V_{GS}=5V$	-	10	-	ns
$t_f$	Fall Time	$R_D=1\Omega$	-	3	-	ns
$C_{iss}$	Input Capacitance	$V_{GS}=0V$	-	360	580	pF
$C_{oss}$	Output Capacitance	$V_{DS}=20V$	-	70	-	pF
$C_{riss}$	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	50	-	pF
$R_g$	Gate Resistance	$f=1.0\text{MHz}$	-	1.67		$\Omega$

**Source-Drain Diode**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{SD}$	Forward On Voltage <sup>2</sup>	$I_S=10A, V_{GS}=0V$	-	-	1.3	V
$t_{rr}$	Reverse Recovery Time <sup>2</sup>	$I_S=10A, V_{GS}=0V$	-	17	-	ns
$Q_{rr}$	Reverse Recovery Charge	$di/dt=100A/\mu s$	-	9	-	nC

**Notes:**

1. Pulse width limited by safe operating area
2. Pulse test - pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$
3. Surface mounted on 1 in<sup>2</sup> copper pad of FR4 board,  $t \leq 10\text{sec}$ ; 150  $^\circ\text{C}/\text{W}$  when mounted on minimum copper pad.

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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Typical Electrical Characteristics

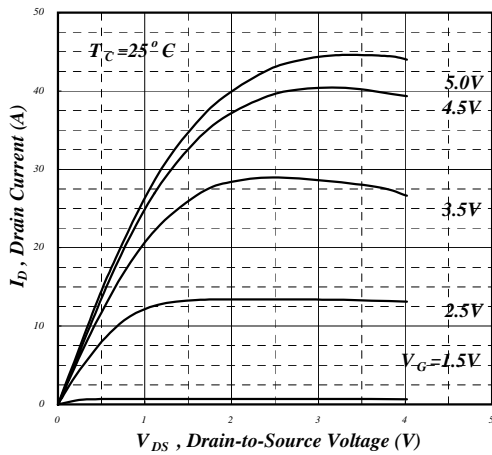


Fig 1. Typical Output Characteristics

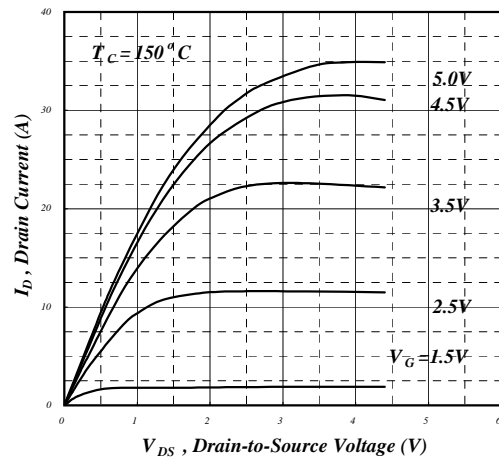


Fig 2. Typical Output Characteristics

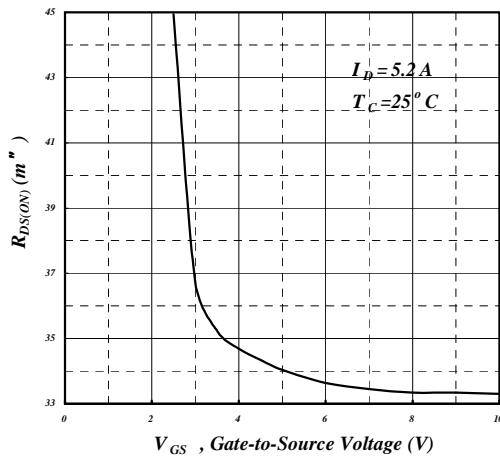


Fig 3. On-Resistance vs. Gate Voltage

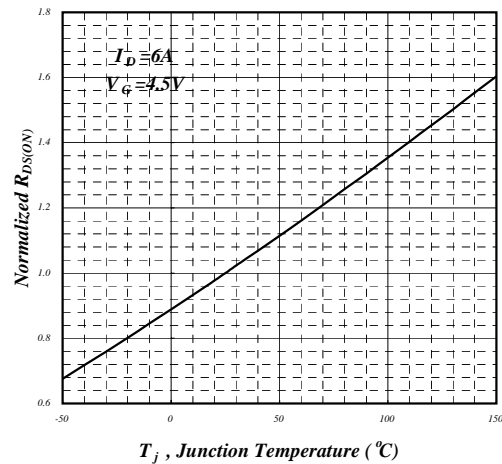


Fig 4. Normalized On-Resistance vs. Junction Temperature

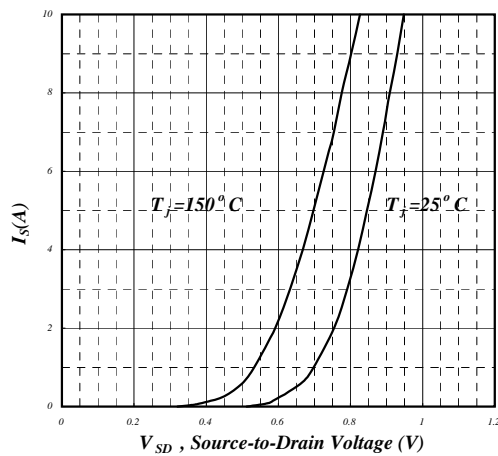


Fig 5. Forward Characteristic of Reverse Diode

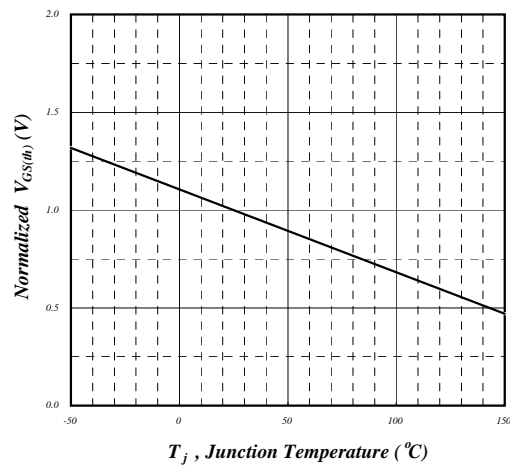


Fig 6. Gate Threshold Voltage vs. Junction Temperature



Typical Electrical Characteristics (cont.)

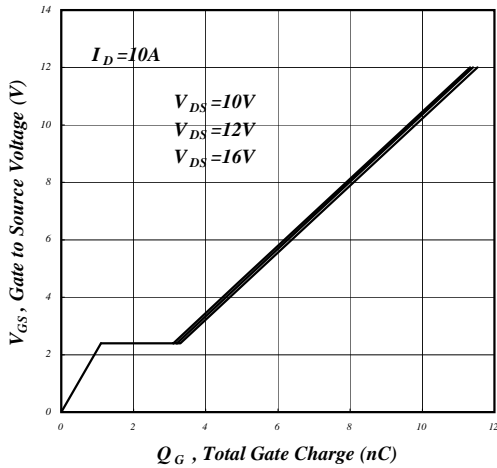


Fig 7. Gate Charge Characteristics

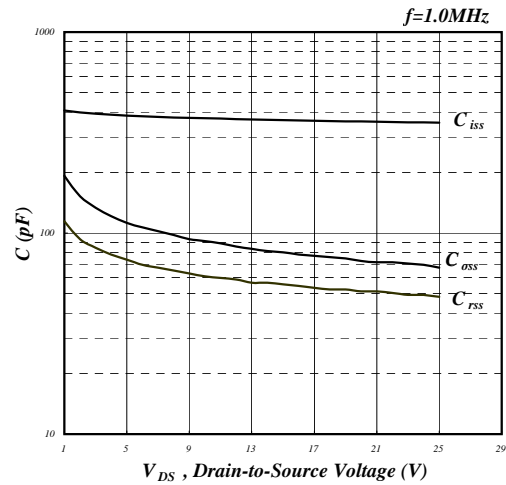


Fig 8. Typical Capacitance Characteristics

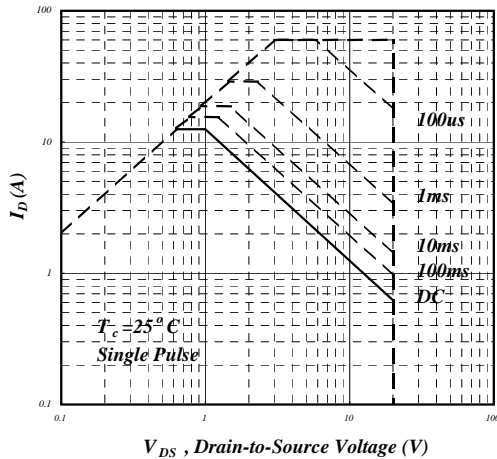


Fig 9. Maximum Safe Operating Area

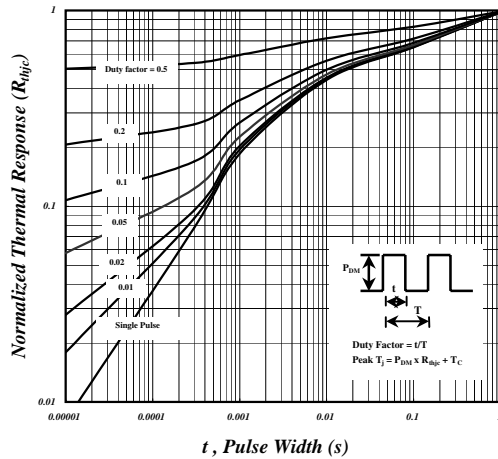


Fig 10. Effective Transient Thermal Impedance

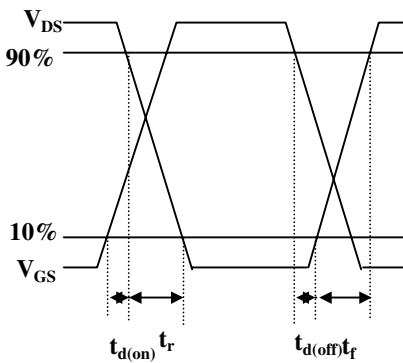


Fig 11. Switching Time Waveforms

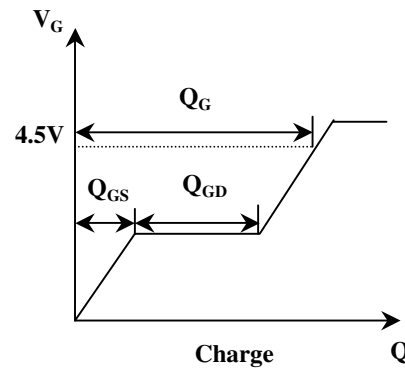
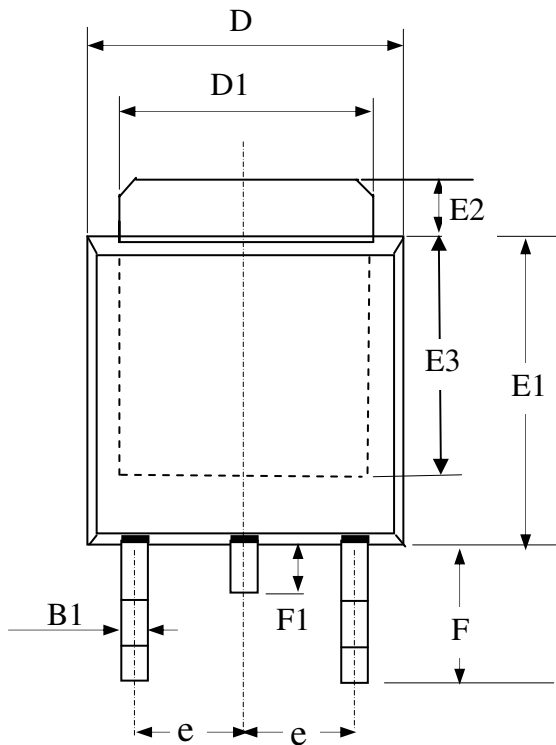


Fig 12. Gate Charge Waveform

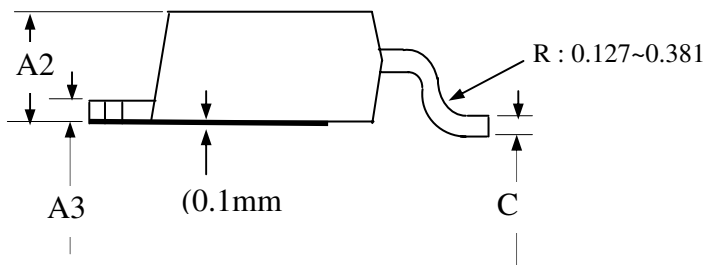


**Package Dimensions: TO-252**



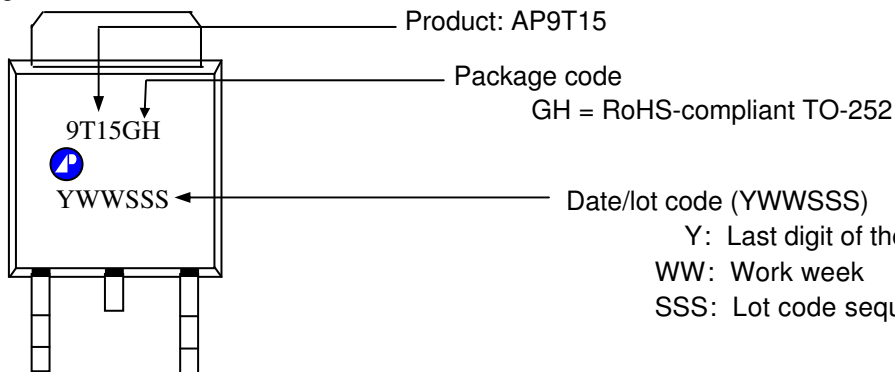
SYMBOLS	Millimeters		
	MIN	NOM	MAX
A2	1.80	2.30	2.80
A3	0.40	0.50	0.60
B1	0.40	0.70	1.00
D	6.00	6.50	7.00
D1	4.80	5.35	5.90
E3	3.50	4.00	4.50
F	2.20	2.63	3.05
F1	0.50	0.85	1.20
E1	5.10	5.70	6.30
E2	0.50	1.10	1.80
e	--	2.30	--
C	0.35	0.50	0.65

1. All dimensions are in millimeters.
2. Dimensions do not include mold protrusions.



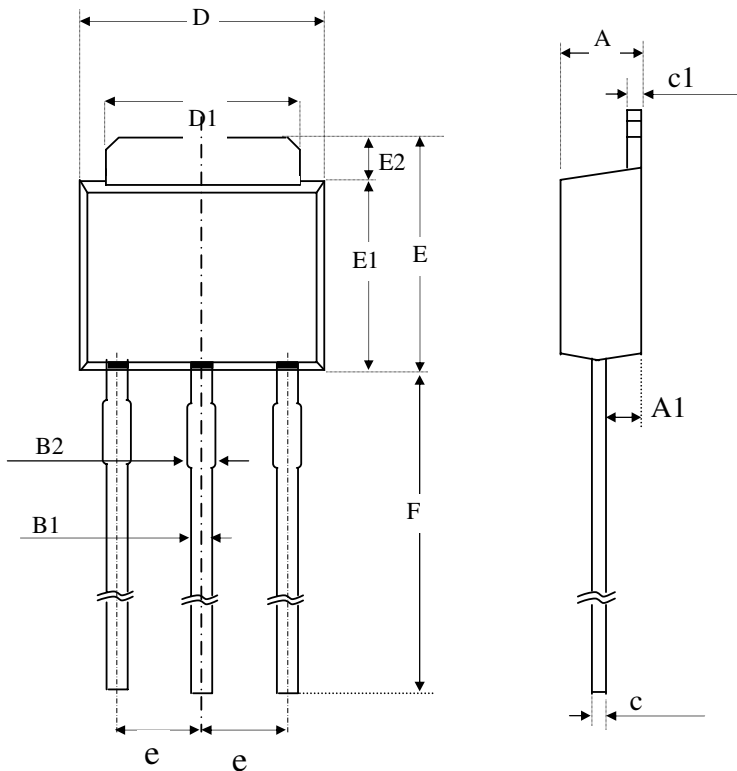
**Marking Information: TO-252**

Laser Marking





**Package Dimensions: TO-251**



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	2.20	2.30	2.40
A1	0.90	1.20	1.50
B1	0.40	0.60	0.80
B2	0.60	0.85	1.05
c	0.40	0.50	0.60
c1	0.40	0.50	0.60
D	6.40	6.60	6.80
D1	4.80	5.20	5.50
E	6.70	7.00	7.30
E1	5.40	5.60	5.80
E2	1.30	1.50	1.70
e	----	2.30	----
F	7.00	8.30	9.60

1. All dimensions are in millimeters.
2. Dimensions do not include mold protrusions.

**Marking Information: TO-251**

